

Surface Mount LEDs

Explanation of Part Number:

H C L - 1 4 0 2 - 4
① ② ③ ④

① Surface mount products kinds:

HCL: chip SMD LEDs.

② Shape distinguish:

140: 1208, with reflector flat top, 3.0(L) X 2.0(W) X 1.0(H) mm.
 150: 1206, flat top, 3.2(L) X 1.6(W) X 1.1(H) mm.
 151: 1206, with lens, 3.0(L) X 1.5(W) X 1.5(H) mm.
 153: 1204, right angle, 3.2(L) X 1.0(W) X 1.5(H) mm.
 155: 1210, flat top dual color, 3.2(L) X 2.7(W) X 1.1(H) mm.
 156: 1210, with lens dual color, 3.0(L) X 2.5(W) X 1.5(H) mm.
 170: 0805, flat top, 2.0(L) X 1.25(W) X 1.1(H) mm.
 190: 0603, flat top, 1.6(L) X 0.8(W) X 0.8(H) mm.
 240: 1206, flat top back light, 3.2(L) X 1.6(W) X 1.1(H) mm.
 420: 1209, with lens, 3.2(L) X 2.4(W) X 2.6(H) mm.

③ Dice kinds:

according to chip characteristic distinguish.
 see below table.

④ Special lens appearance:

1: colored diffusion.
 2: colored clear.
 3: white diffusion.
 4: water clear

Ta=25°C

Type	Material	Absolute Maximum Rating				Electro-Optical Characteristics								
		Pd	If	IFM	VR	wavelength			forward voltage		reverse current			
						λp	λd	Δλ	If	typ	Max	If	Max	VR
2	GaP/GaP	90	20	50	5	700	658	100	20	2.20	2.80	20	10	5
3 ,DG,CG	GaP/GaP	84	25	50	5	570	567	30	20	2.15	2.80	20	10	5
3PG	GaP/GaP	84	25	50	5	557	560	25	20	2.25	2.80	20	10	5
3BG	AllnGaP/GaAs	100	25	50	5	575	572	20	20	2.20	2.40	20	10	5
3BGA	GalnN/SiC	135	30	100	5	502	505	30	20	3.50	4.00	20	10	5
3AG	GalnN/GaN	120	30	100	5	523	525	45	20	3.50	4.00	20	10	5
4	GaAsP/GaP	90	25	50	5	589	585	35	20	2.10	2.80	20	10	5
4AY	AllnGaP/GaAs	100	25	50	5	589	588	25	20	2.00	2.40	20	10	5
4AYL	AllnGaP/GaAs	100	25	50	5	593	591	25	20	2.00	2.40	20	10	5
5	GaAsP/GaP	90	30	50	5	625	618	45	20	2.05	2.80	20	10	5
5AO	AllnGaP/GaAs	100	25	50	5	620	615	20	20	2.00	2.60	20	10	5
5AOR	AllnGaP/GaAs	100	25	50	5	635	626	25	20	2.00	2.50	20	10	5
6 DR,CR	GaAlAs/GaAs	110	30	50	5	660	643	30	20	1.80	2.40	20	10	5
6BR	AllnGaP/GaAs	100	25	50	5	655	638	25	20	2.10	2.60	20	10	5
6AR	GaAlAs/GaAlAs	110	25	50	5	660	645	20	20	1.86	2.50	20	10	5
7	GaAsP/GaP	90	30	50	5	610	606	35	20	2.05	2.60	20	10	5
7AA	AllnGaP/GaAs	100	25	50	5	607	605	20	20	2.00	2.40	20	10	5
8CB	GalnN/SiC	135	30	100	5	468	470	26	20	3.80	4.20	20	10	5
8AB	GalnN/GaN	120	30	100	5	465	470	35	20	3.50	4.00	60	10	4
9CW	GalnN/SiC	135	30	100	5	---	---	---	---	3.80	4.20	20	10	5
9AW	GalnN/GaN	120	30	100	5	---	---	---	---	3.60	4.00	60	10	4
unit		mW	mA	mA	V	nm	nm		mA	V	V	mA	uA	V

IFM condition: 1/10 duty cycle, pulse width =0.1ms.